

Amendments to the Specification

Please replace the Abstract with the following new Abstract:

A semiconductor device manufacturing method comprises a first step of forming, by a thermal chemical vapor deposition method, a silicon nitride film on an object disposed in a reaction container, with bis tertiary butyl amino silane and NH₃ flowing into the reaction container, and a second step of removing silicon nitride formed in the reaction container, with NF₃ gas flowing into the reaction container.